

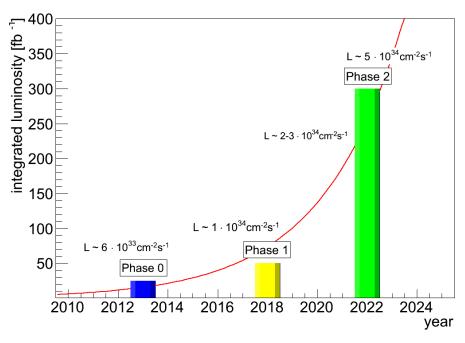
# ATLAS Semiconductor Tracker Upgrade

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**IOP 2013 Liverpool** 



#### **LHC Upgrade Luminosity**



#### Phase 2 (2022)

- High-Luminosity LHC (HL-LHC)
- Expected to reach  $5 \times 10^{34} cm^{-2}s^{-1}$
- Centre-of-mass energy  $\sqrt{s} = 14 \, TeV$
- Average 140 proton-proton interactions



#### The ITk Upgrade

- End of the life time for the Inner Detector
- Redesign to withstand harsher conditions
  - Higher particle count
  - Higher radiation dosage
- All Silicon tracker
  - A balance between measurement precision and material profile
- Two Subsystems
  - Pixel layer
  - Silicon Microstrip layer

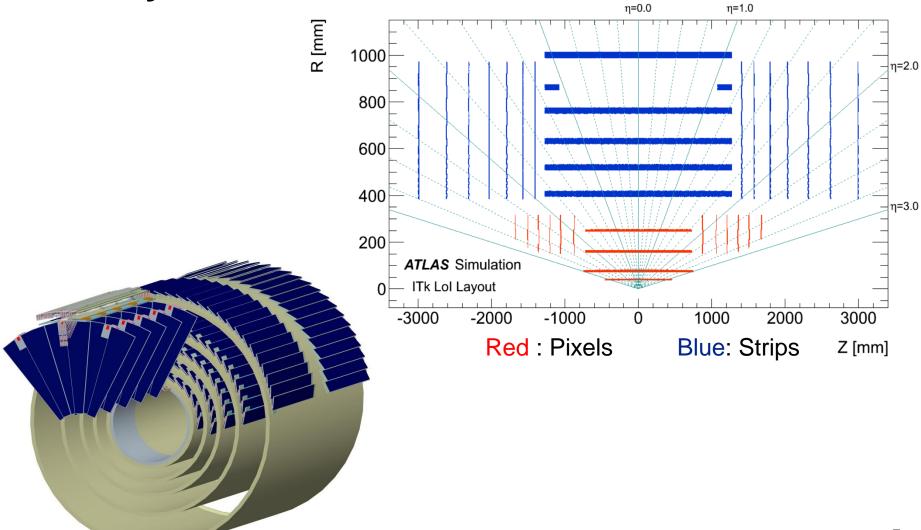


#### **Strip System**

- 5 Barrel layers surrounding the pixel layer.
  - Radii 405mm → 1000mm
- 7 Endcap disks
  - at z-positions  $\pm 1415$ mm  $\rightarrow \pm 3000$ mm.
- 2 Stub cylinders
  - between 4<sup>th</sup> and 5<sup>th</sup> barrel layer
- Every layer provides 2 hits (Slide 6)
- 10 possible hits per track in the region  $|\eta| < 2.5$  (+4 from pixels)
  - Track reconstruction requires 11

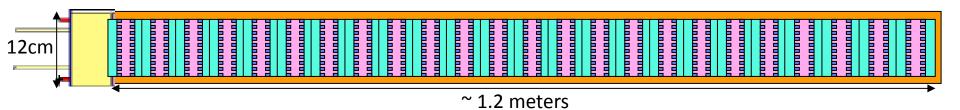


#### **ITk Layout**

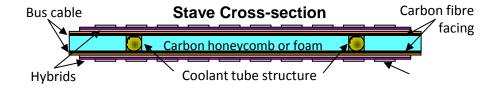


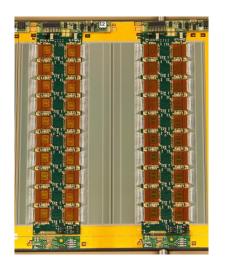


#### **Stave Concept**



- Reduction in material
- Designed for mass production





#### Module

- ~10cmx10cm n-in-p sensor
- 4 columns ~2.5cm each
- Two glued hybrids
- 20 ABCN-250 chips per hybrid
- 128 channels per chip



#### **Stavelet**

- Shortened stave
  - Proof of concept
- 4 modules in a stavelet
- 2 types of system powering
  - Serial powered
  - DCDC powered (<u>reporting on this</u>)
- Readout through HSIO board





#### **Standard Tests**

#### Strobe delay

 determines the correct Strobe Delay setting, corresponding to the timing of the charge injection pulse. To ensure the clock frequency will be synchronous with the pulse.

#### 3pointGain

Threshold scans are performed for three different injected charges.
 The resulting response curve is fitted linearly to obtain values for its estimated discriminator offset, the channels gain and noise.

#### Noise occupancy

Measures the noise occupancy as a function of threshold.

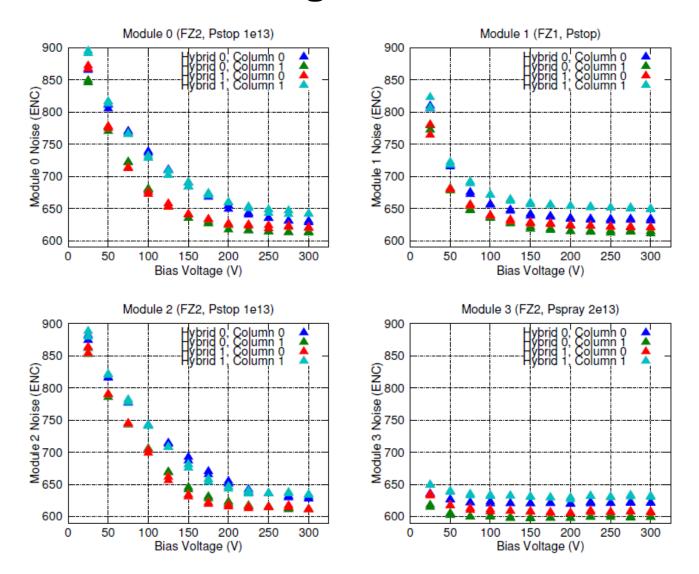


#### Noise vs. Variables

- Noise measured with 3pointGain scans at 1fC
- Noise reported as Electron Noise Count (ENC)
- Variables
  - Bias Voltage, Temperature, Low Voltage.

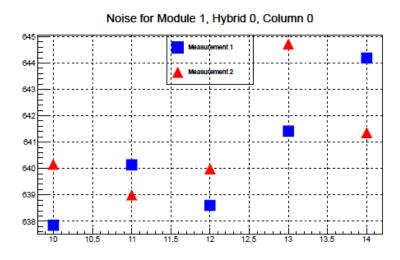


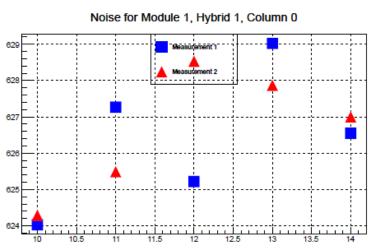
#### Noise vs. Bias Voltage<sup>1</sup>

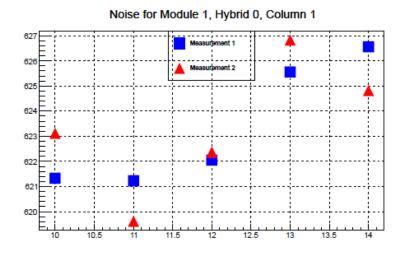


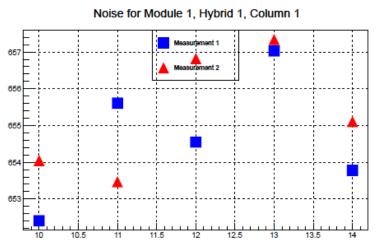


### Noise vs. Low Voltage<sup>1</sup>



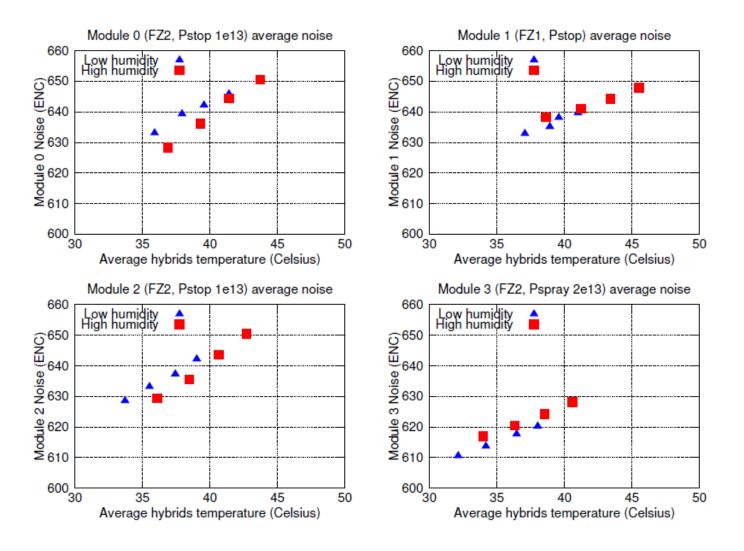








### Noise vs. Temperature<sup>1</sup>





#### Stavelet's E-H field Susceptibility

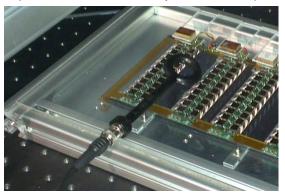


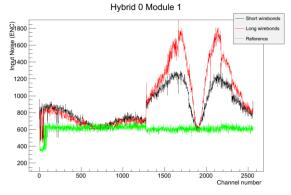
- DCDC converter is the main source of E-H fields.
- Shielding required
  - Thinnest possible. Minimize material budget
- H-field require thick shield
- E-field can be attenuated with a thin shield



#### H-field

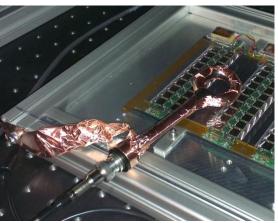
# Non-grounded H-field loop probe (-45dBm 4MHz Square wave)





- Saddle shaped noise due to the geometry of the probe
- Noise shown for 1 hybrid (2 columns)

Shielded and Grounded loop probe (-45dBm 4MHz Square wave)

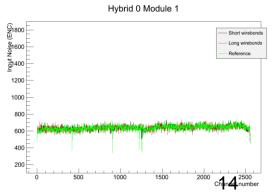


Disappearance of the noise due to the absence of the E-field

#### Placed on top of the DCDC converter

# Hybrid 1 Module 0 Short wirebonds Long wirebonds Long wirebonds Reference 1200 1000 1000 1500 2000 2500

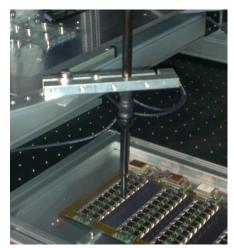
#### Placement as shown above

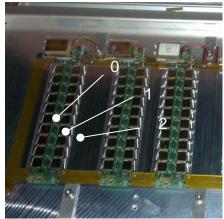


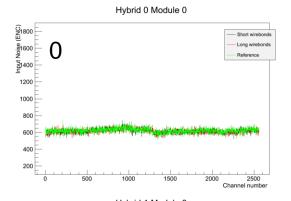


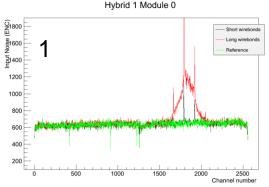
#### E-field

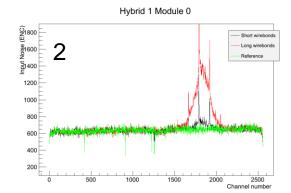
- Stub E-field probe pointing towards a module
- Driven with a 4MHz square wave
- Effective output -65dBm
- Stub probe produces a narrow E-field
- Stub probe was positioned at three different points











 Field too narrow to reach any of the wirebonds

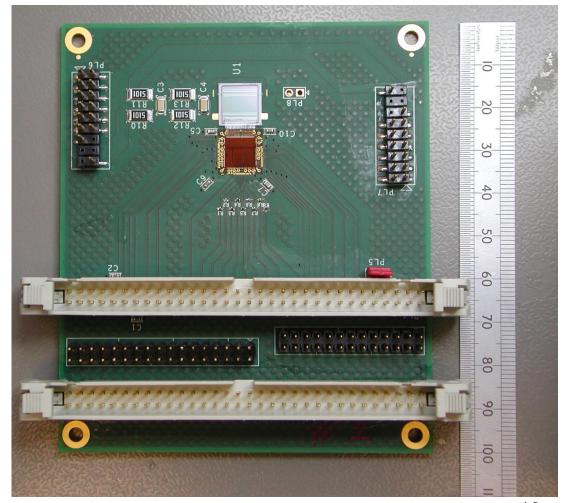
The field only covers the area around the chip. Only the long wirebonds are exposed to it while shielding the short bonds.

The field is on top of the area where the wires are bonded to the strips. Both long and short wirebonds are exposed.



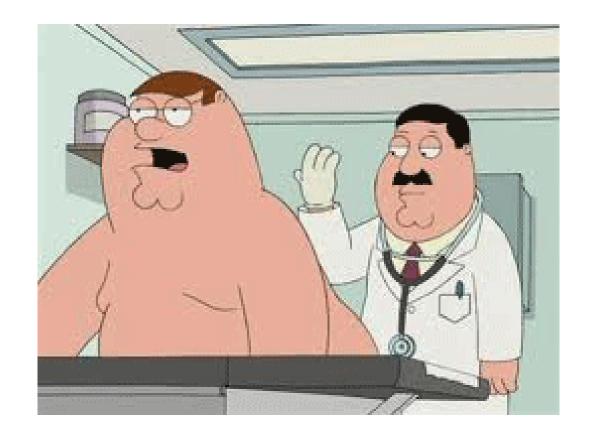
#### **Laser Tests @ RAL**

- Mini sensor wirebonded to a ABCN-250 chip
- Laser 1064nm50µJ
- Test to see how much charge the chip can handle
- Final tests with ABCN130





#### **Questions?**





#### References

- 1. DC-DC Stavelet Studies in CERN B180, C. A. Garcia, ATLAS Upgrade Week, SLAC, 27/03/2012
- 2. ATLAS Strip Tracker Stavelets, P. W. Philips, TWEPP, Vienna, 26/09/2011
- 3. ATLAS Inner Tracker LoI, S. Burdina et al, CERN, 11/02/2013
- 4. Electrical Tests of SCT Hybrids and Modules, P. W. Phillips et al, CERN, 14/11/2000.



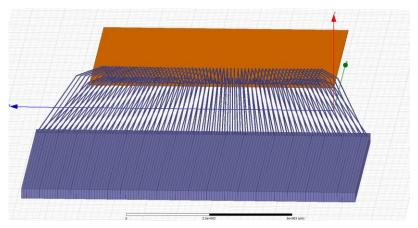
## **Backup slides**

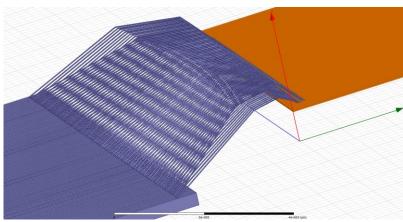
#### **ABCN130**

- 256 Input channels
  - ABCN-250 128 Input channels
- 130nm CMOS technology
- 1.3V external power supply
- Three Trigger types, L0, R3 and L1 control the data flow.
- Xon / Xoff flow control between chips.
- Readout clock up to 160Mbits/sec
- Readout mode compatible with an external Hybrid Controller Chip, HCC
- SEU errors handling
- Fast cluster finder logic

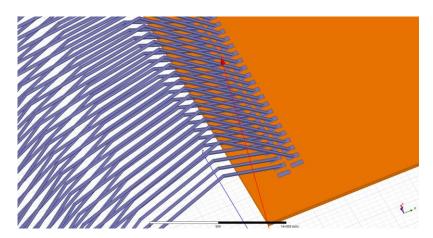


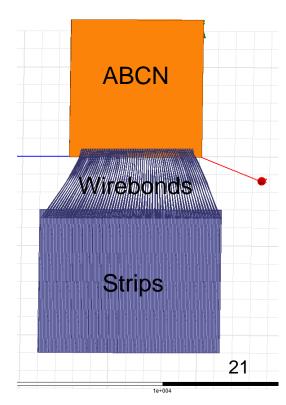
#### Simulation (Model)





- Full model drawn in Ansoft HFSS
- Due to limited computing resources model was halved.







# Simulation (Solution)

